



Bipolar PNP Bare Die – BTP6973

Part Description

The BTP6973 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6973

Key Parameters:

- VCBO = -40V
- VCEO = -40V
- VEBO = -5V
- hFE = 300-600 @ VCE = -2V, IC = -0.1A
- VCE(Sat) = -0.255V @ IC = -1A, IB = -50mA
- fT = 100 MHz @ VCE = -10V, IE = 0A
- COBO = 28pF @ VCB = -10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to NXP / NEXPERIA PBSS5240T

Die Size (Unawn)

700µm X 700µm, 28 Mils X 28 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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